

**Amendments to th Claims**

Claims 1-53 (Cancelled).

54. (Original) A method of forming a conductive contact comprising:  
forming an insulative material over a silicon comprising substrate;  
forming an opening into the insulative material over a node location on the silicon comprising substrate to which electrical connection is desired;  
first plasma etching within the opening using a gas chemistry comprising hydrogen and exposing silicon of the substrate to said plasma hydrogen;  
after the first plasma etching, second plasma etching within the opening using a gas chemistry comprising chlorine; and  
after the second plasma etching, forming a silicide material within the opening in contact with silicon of the substrate.

55. (Original) The method of claim 54 wherein the silicide material is formed by refractory metal deposition and anneal.

56. (Original) The method of claim 54 wherein the silicide material is formed by chemical vapor deposition of the silicide material.

57. (Original) The method of claim 54 wherein the gas chemistry comprising hydrogen comprises H<sub>2</sub>.

58. (Original) The method of claim 54 wherein the gas chemistry comprising chlorine comprises Cl<sub>2</sub>.

59. (Original) The method of claim 54 wherein the gas chemistry comprising chlorine comprises HCl.

60. (Original) The method of claim 54 wherein the first plasma etching, the second plasma etching, and at least some of the silicide material forming all occur in the same chamber.